

2N5020, 2N5021

P-Channel Silicon Junction Field-Effect Transistor

• Analog Switches

Absolute maximum ratings at $T_A = 25^\circ\text{C}$

Reverse Gate Source & Reverse Gate Drain Voltage	– 50 V
Continuous Forward Gate Current	50 mA
Continuous Device Power Dissipation	500 mW
Power Derating	4 mW/°C
Storage Temperature Range	– 65°C to + 200°C

At 25°C free air temperature:

Static Electrical Characteristics

		2N5020		2N5021		Process PJ32		
		Min	Max	Min	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	$V_{(BR)GDO}$	25		25		V	$I_G = 1\mu\text{A}$, $V_{DS} = \emptyset\text{V}$	
Gate Reverse Current	I_{GSS}		1		1	nA	$V_{GS} = 15\text{V}$, $V_{DS} = \emptyset\text{V}$	
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	0.3	1.5	0.5	2.5	V	$V_{DS} = -15\text{V}$, $I_D = 1\text{nA}$	
Drain Saturation Current (Pulsed)	I_{DSS}	– 0.3	– 1.2	– 1	– 3.5	mA	$V_{DS} = -15\text{V}$, $V_{GS} = \emptyset\text{V}$	

Dynamic Electrical Characteristics

Common Source Forward Transconductance	g_{fs}	1	3.5	1.5	6	mS	$V_{DS} = -15\text{V}$, $V_{GS} = \emptyset\text{V}$	
Common Source Output Conductance	g_{os}		20		20	μS	$V_{DS} = -15\text{V}$, $V_{GS} = \emptyset\text{V}$	
Common Source Input Capacitance	C_{iss}		25		25	pF	$V_{DS} = -15\text{V}$, $V_{GS} = \emptyset\text{V}$	f = 1 MHz
Common Source Reverse Transfer Capacitance	C_{rss}		7		7	pF	$V_{DS} = -15\text{V}$, $V_{GS} = \emptyset\text{V}$	f = 1 MHz

TO-18 Package

Dimensions in Inches (mm)

Pin Configuration

1 Source 1, 2 Gate & Case, 3 Drain

Surface Mount

SMP5020, SMP5021



InterFET Corporation

1000 N. Shiloh Road, Garland, TX 75042
 (972) 487-1287 FAX (972) 276-3375

www.interfet.com